





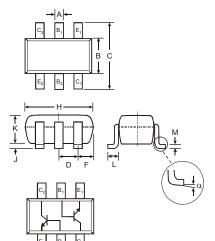
DUAL NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- **Epitaxial Planar Die Construction**
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 2)
- "Green" Device (Note 3 and 4)

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)



	SOT-363									
Dim	Min	Max								
Α	0.10	0.30								
В	1.15	1.35								
С	2.00 2.20									
D	0.65 Nominal									
F	0.30	0.40								
Н	1.80	2.20								
J	_	0.10								
K	0.90	1.00								
L	0.25	0.40								
М	0.10	0.25								
α	α 0° 8°									
All Dimensions in mm										

Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous	I _C	200	mA
Power Dissipation (Note 1)	P _d	200	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	625	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Notes:

- 1. Device mounted on FR-4 PCB; pad layout as shown on Diodes Inc. suggested pad layout documents APO2001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

 Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.



Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60	_	V	$I_C = 10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40	_	V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5.0	_	V	$I_E = 10 \mu A, I_C = 0$
Collector Cutoff Current	I _{CEX}		50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V
Base Cutoff Current	I _{BL}		50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V
ON CHARACTERISTICS (Note 5)	•	•			
DC Current Gain	h _{FE}	40 70 100 60 30	 300 	l	$\begin{split} I_{C} &= 100 \mu A, V_{CE} = 1.0 V \\ I_{C} &= 1.0 m A, V_{CE} = 1.0 V \\ I_{C} &= 10 m A, V_{CE} = 1.0 V \\ I_{C} &= 50 m A, V_{CE} = 1.0 V \\ I_{C} &= 100 m A, V_{CE} = 1.0 V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.20 0.30	>	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65	0.85 0.95	V	$I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 50$ mA, $I_B = 5.0$ mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	_	4.0	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C_{ibo}	_	8.0	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_C = 0$
Input Impedance	h _{ie}	1.0	10	kΩ	
Voltage Feedback Ratio	h _{re}	0.5	8.0	x 10 ⁻⁴	V _{CE} = 10V, I _C = 1.0mA,
Small Signal Current Gain	h _{fe}	100	400	_	f = 1.0kHz
Output Admittance	h _{oe}	1.0	40	μS	
Current Gain-Bandwidth Product	f⊤	300		MHz	V _{CE} = 20V, I _C = 10mA, f = 100MHz
Noise Figure	NF		5.0	dB	V_{CE} = 5.0V, I_{C} = 100μA, R_{S} = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	_	35	ns	V _{CC} = 3.0V, I _C = 10mA,
Rise Time	tr	_	35	ns	$V_{BE(off)} = -0.5V$, $I_{B1} = 1.0mA$
Storage Time	ts	_	200	ns	V _{CC} = 3.0V, I _C = 10mA,
Fall Time	t _f	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$

Notes: 5. Short duration pulse test used to minimize self-heating.



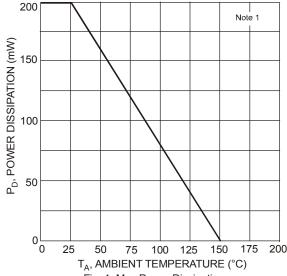
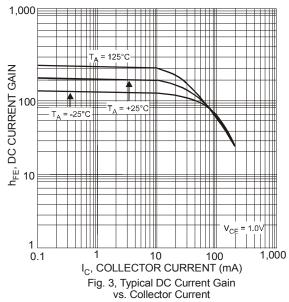


Fig. 1, Max Power Dissipation vs. Ambient Temperature (Total Device)



10 V_{BE(SAT)}, BASE-EMITTER (V) SATURATION VOLTAGE 0.1 <u></u> 1 10 100 I_C, COLLECTOR CURRENT (mA) 1,000

Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

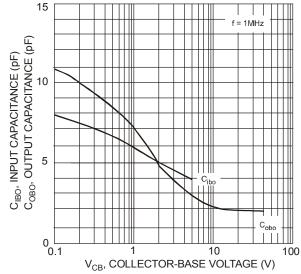


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

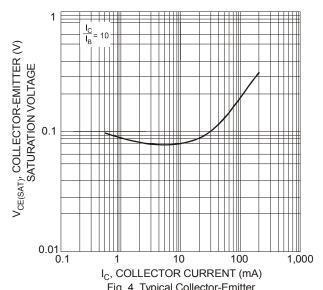


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

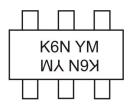


Ordering Information (Note 6)

Device	Packaging	Shipping		
MMDT3904-7-F	SOT-363	3000/Tape & Reel		

6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K6N = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Х	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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